

Professor Oldham

Fall 1999

EECS 40 — MIDTERM #2

10 November 1999

Name: _____
Last, First

Student ID: _____

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Guidelines:

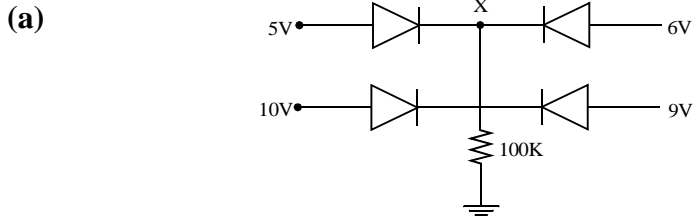
1. Closed book and notes except 1 page of formulas.
2. You may use a calculator.
3. Do not unstaple the exam.
4. Show *all your work and reasoning on the exam* in order to receive full or partial credit.
5. This exam contains 12 pages plus the cover page and 2 sheets of scratch paper included at the end of the exam. You can remove these from the rest of the exam if you wish.

Problem	Points Possible	Your Score
1	20	
2	20	
3	20	
4	20	
5	20	
Total	100	

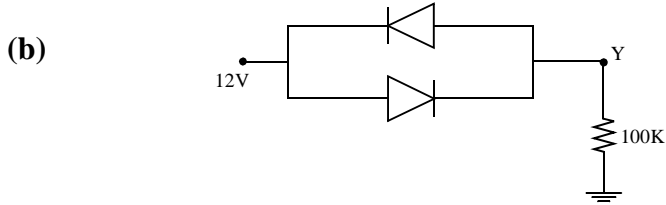
$K = 10^3$
$m = 10^{-3}$
$\mu = 10^{-6}$
$n = 10^{-9}$
$p = 10^{-12}$
$f = 10^{-15}$

Problem 1 (20 points)

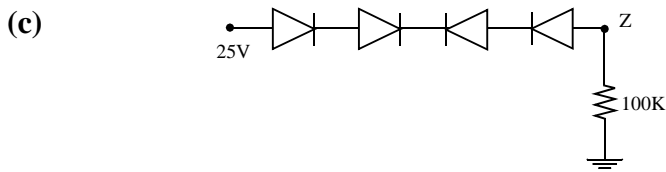
What is the value of the unknown node voltage in each of the following circuits? Assume diodes are perfect rectifiers.



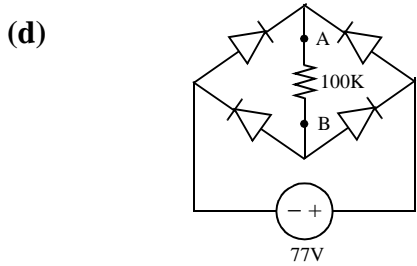
$V_X =$ _____



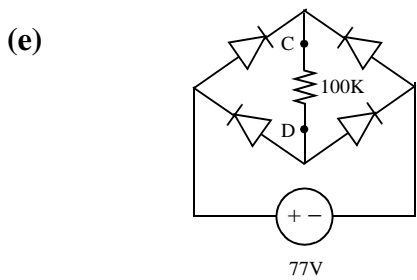
$V_Y =$ _____



$V_Z =$ _____



$V_{AB} =$ _____



$V_{CD} =$ _____

(f) A cross-section for a CMOS chip is shown on the facing page. Some node voltages are indicated. Please tell us what the values are for the node voltages at nodes U, W, R, S.

$V_U =$ _____

$V_W =$ _____

$V_R =$ _____

$V_S =$ _____

Prob. 1 Worksheet

Problem 2 (20 points)

Shown on the opposite page is the layout and two cross-sections through a CMOS inverter. A list of components follows. You are to indicate, by labelling, the location of that feature on the figure. The first question is used as an example.

2.1 Layout

- (1) A contact to polysilicon [EXAMPLE]
- (2) gate of NMOS transistor
- (3) the W dimension of the PMOS transistor
- (4) contact to p-type substrate
- (5) metal contact to PMOS gate
- (6) spacing from n+ source drain areas to well mask
- (7) input electrode
- (8) output electrode


2.2 Cross-sections

- (a) well region
- (b) field oxide
- (c) NMOS gate oxide
- (d) metal contact to PMOS source or drain
- (e) poly on field oxide
- (f) metal over field oxide
- (g) contact to NMOS source or drain
- (h) oxide over polysilicon gate

2.3 Masks

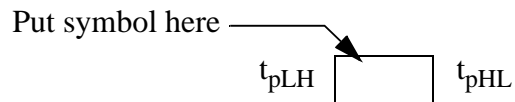
A possible list of masks for this process follows. You are to order the masks by simply filling in the mask number. It is possible that one or more masks is missing. If so, you must fill out a new mask row for each missing mask.

MASK#	NAME	FUNCTION
	Poly	Define polysilicon areas
	N-select	Define n+ implant areas
	P-select	Define p+ implant areas
	Oxide	Define areas for gate oxide
	Metal	Define metal conductor pattern

Fill in mask # here 

2.4 Gate delay

For this layout, what do we expect for the relationship between gate delay for output rising (t_{pLH}), and output falling (t_{pHL})? Answer by putting in the correct symbol in the box (=, >, or <).

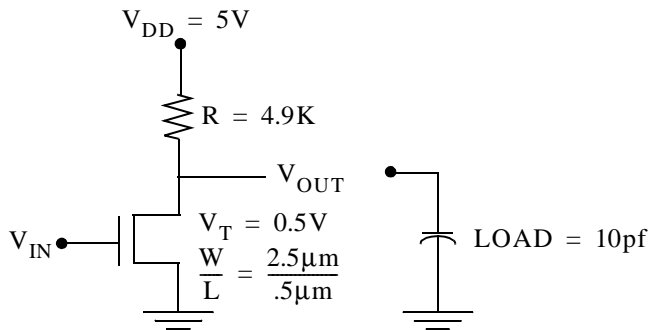


Why? _____

Prob. 2 – Schematic for CMOS Inverter

Problem 3 (20 points)

You are trying to construct a dc switch with an MOS transistor, as shown below. The idea: When input is low, output high. But when input is high, output is hopefully low.



Note: For this transistor

$$C_{ox} = 10\text{fF}/\mu\text{m}^2 = 1\mu\text{F}/\text{cm}^2$$

$$\mu = 1000 \frac{\text{cm}^2}{\text{V sec}} \text{ for electrons}$$

- (a) If $V_{IN} = 5\text{V}$, what is the channel electron charge ($\text{coulomb}/\text{cm}^2$)(for small values of V_{OUT} only)?

formula _____

value _____

- (b) If $V_{IN} = 5\text{V}$, what is the sheet resistance of the channel? (Again for the case in which V_{OUT} is very small.)

formula _____

value _____

- (c) What is the value of V_{IN} needed to produce an output of 0.1 V?

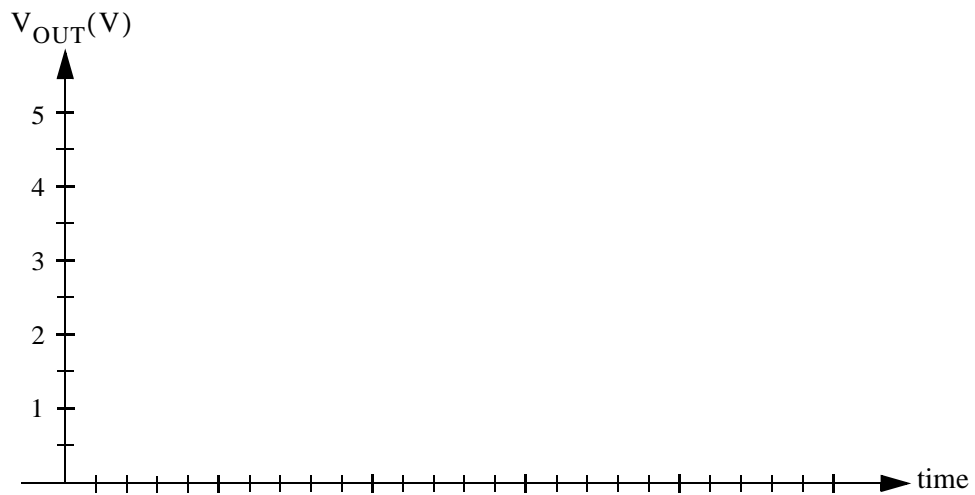
$V_{IN} =$ _____

- (d) If the input suddenly switches low, and the load is 10 pF, as shown, sketch the output voltage versus time (accurately) and estimate the time Δt for the output to go from 0.1 V to 2.45V (halfway to 5 V).

$\Delta t =$ _____ n sec

Problem 3 Answer Sheet

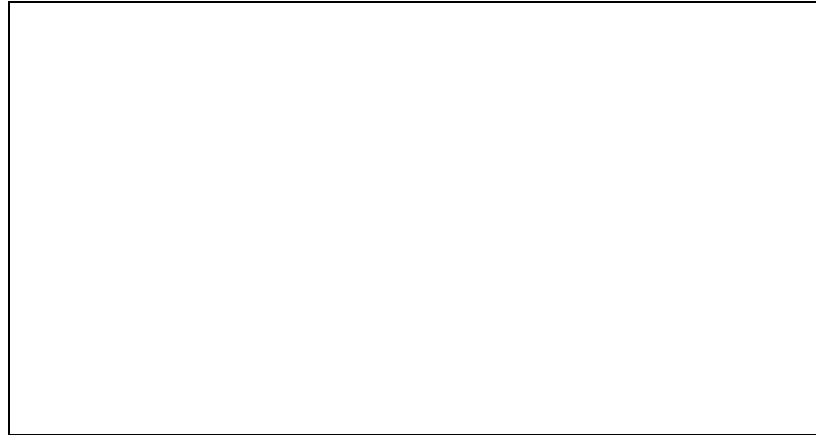
(d)



Prob. 4 Answer Sheet (Parts a, b, c)

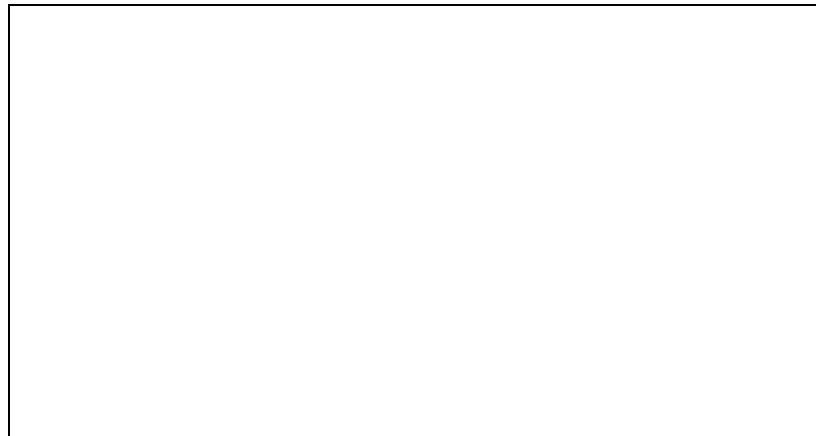
(a)

PUT CIRCUIT
HERE →
for $V_{IN} = 3V$

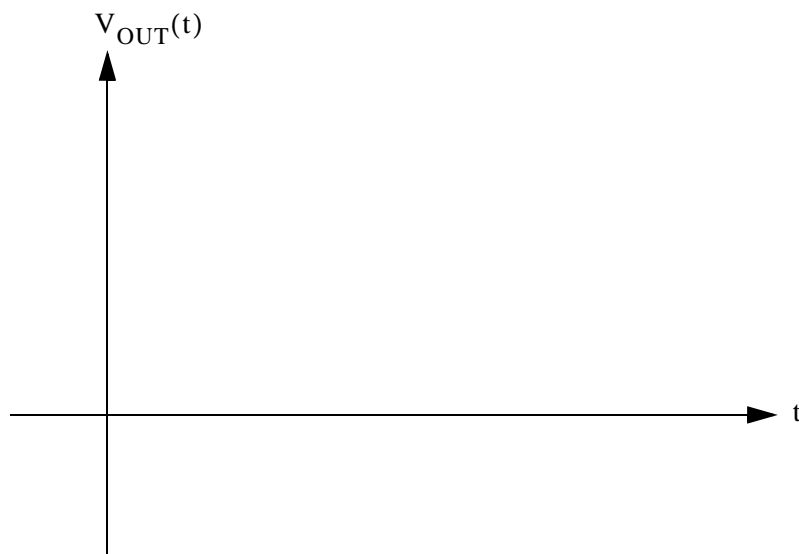


(b)

PUT CIRCUIT
HERE →
for $V_{IN} = 0$



(c)



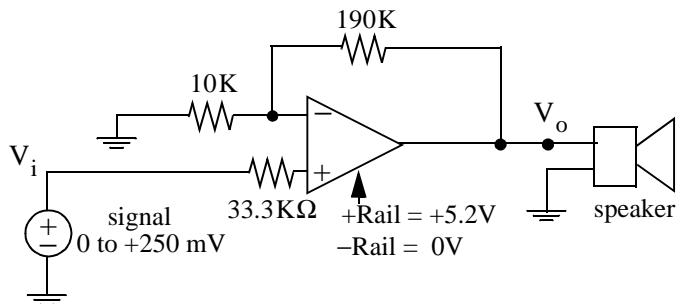
Problem 5 (20 points)

(a) You open up your Robot Kit and find the following circuit. You suspect it is a linear voltage amplifier. You know the differential amplifier has very high internal gain.

(a.1) Is it a linear amplifier?

(a.2) If so, what is the voltage gain $\frac{V_o}{V_i}$? [If not, ignore (a.2).]

(a.3) If not, why not?



Linear amplifier? (Yes or No) _____

$$A_V \equiv \frac{V_o}{V_i} = \underline{\hspace{2cm}}$$

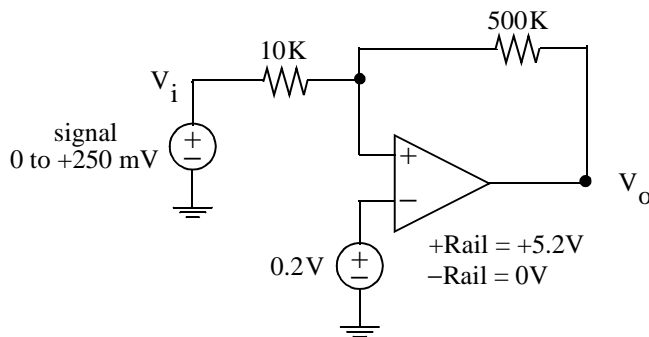
If not, why not? _____

(b) You also find the following circuit. Again you suspect a linear amplifier. You know the differential amplifier has very high internal gain.

(b.1) Is it a linear amplifier?

(b.2) If so, what is the voltage gain? [If not, ignore (b.2).]

(b.3) If not, why not?



Linear amplifier? (Yes or No) _____

$$A_V \equiv \frac{V_o}{V_i} = \underline{\hspace{2cm}}$$

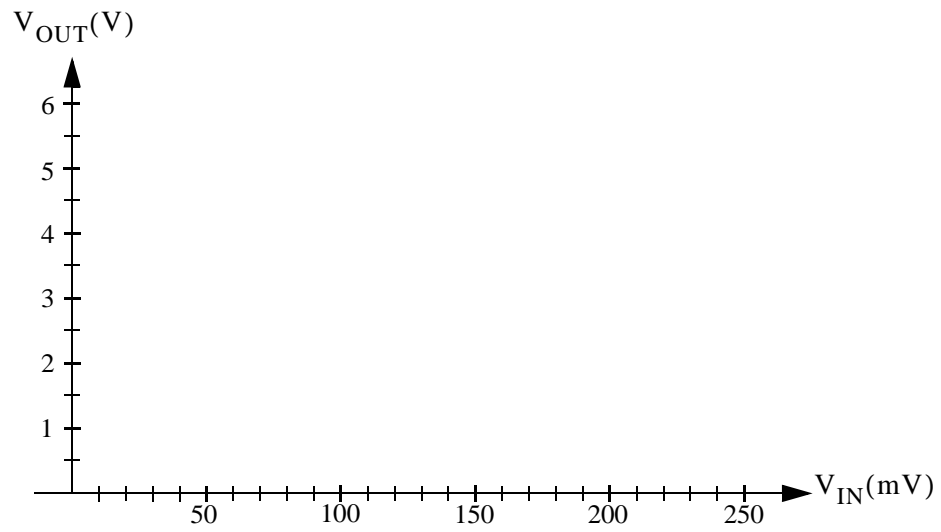
If not, why not? _____

(c) Carefully sketch the curve of V_{OUT} versus V_{IN} for circuit (a) on the graph axes provided for $0 \leq V_i \leq 250\text{mV}$.

(d) Carefully sketch the curve of V_{OUT} versus V_{IN} for circuit (b) on the graph axes provided for $0 \leq V_i \leq 250\text{mV}$.

Prob. 5. Answer Sheet

(c)



(d)

